

• General Description

The ZM130P03M combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

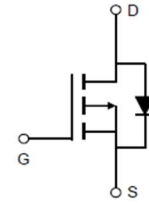
• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- Load Switch
- PWM Application
- BLDC Motor driver

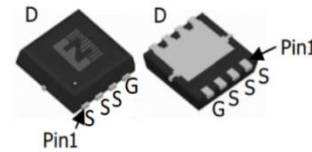
• Product Summary



$$V_{DS} = -30V$$

$$R_{DS(ON)} = 13m\Omega$$

$$I_D = -30A$$



DFN3 x 3

• Ordering Information:

Part NO.	ZM130P03M
Marking	130P03
Packing Information	REEL TAPE
Basic ordering unit (pcs)	5000

• Absolute Maximum Ratings ($T_c = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	-30	A
	$I_{D@TC=75^\circ C}$	-23	A
	$I_{D@TC=100^\circ C}$	-19	A
Pulsed Drain Current ^①	I_{DM}	-60	A
Total Power Dissipation ^②	$P_{D@TC=25^\circ C}$	17	W
Total Power Dissipation	$P_{D@TA=25^\circ C}$	1.8	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy@L=0.1mH	E_{AS}	80	mJ
Avalanche Current@L=0.1mH	I_{AS}	-30	A

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case ^②	R_{thJC}	-	-	7.3	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	70	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\mu A$	-1.2		-2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = -30V, V_{GS} = 0V$			-1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = -10V, I_D = -9A$		13	15	m Ω
		$V_{GS} = -4.5V, I_D = -8A$		22	25	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = -10V, I_D = -5A$		9		s
Diode Forward Voltage	V_{FSD}	$I_S = -9A$			1.2	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$V_{DS} = -15V$ $f = 1MHz$	-	1650	-	pF
Output capacitance	C_{oss}		-	330	-	
Reverse transfer capacitance	C_{rss}		-	220	-	

•Gate Charge characteristics($T_a = 25^\circ C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = -15V$ $I_D = -9A$ $V_{GS} = -10V$	-	18	-	nC
Gate - Source charge	Q_{gs}		-	6	-	
Gate - Drain charge	Q_{gd}		-	7	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

Fig.1 Gate-Charge Characteristics

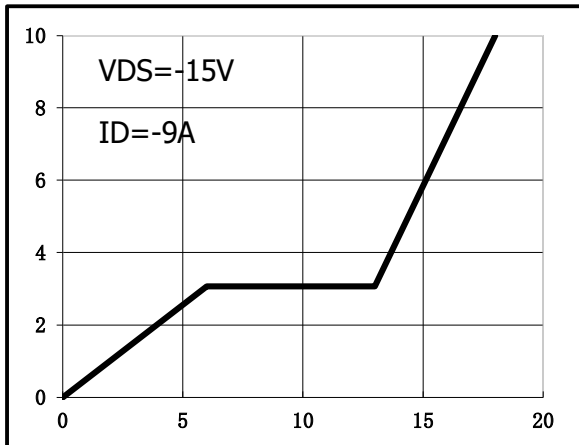


Fig.2 Capacitance Characteristics

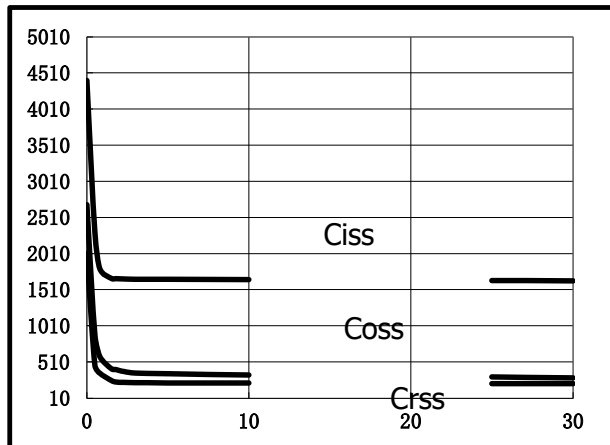


Fig.3 Power Dissipation Derating Curve

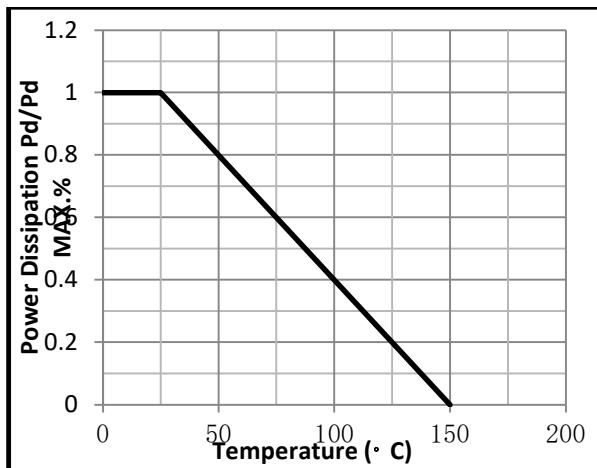


Fig.4 Typical output Characteristics

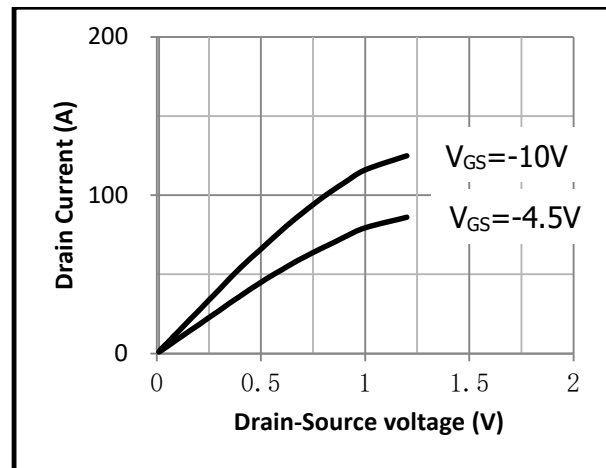


Fig.5 Threshold Voltage V.S Junction Temperature

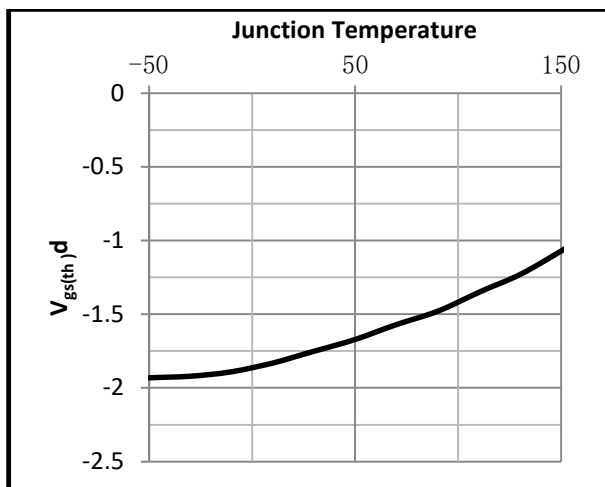


Fig.6 Resistance V.S Drain Current

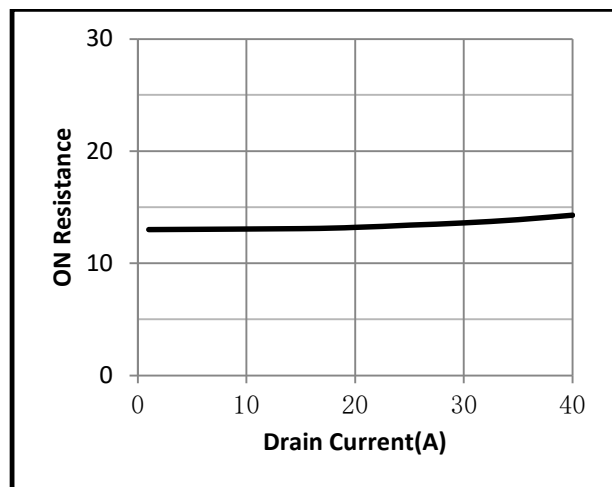


Fig.7 On-Resistance VS Gate Source Voltage

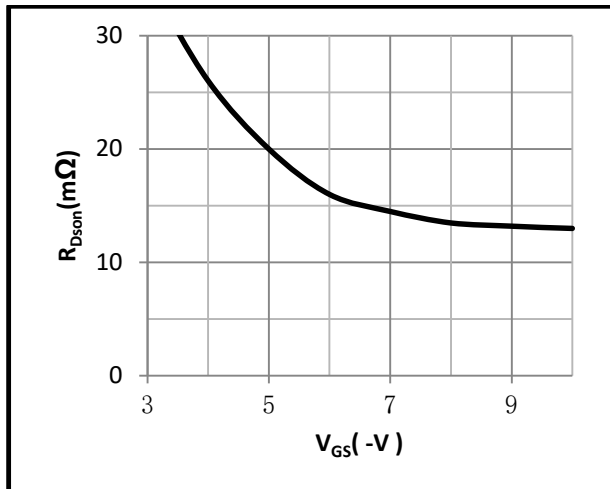


Fig.8 On-Resistance V.S Junction Temperature

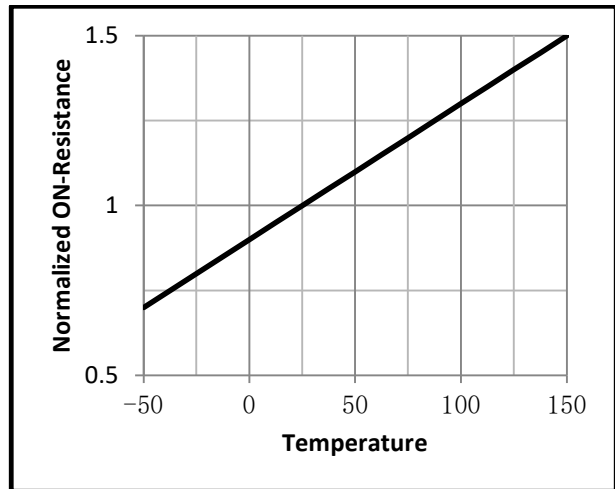


Fig.9 Gate Charge Measurement Circuit

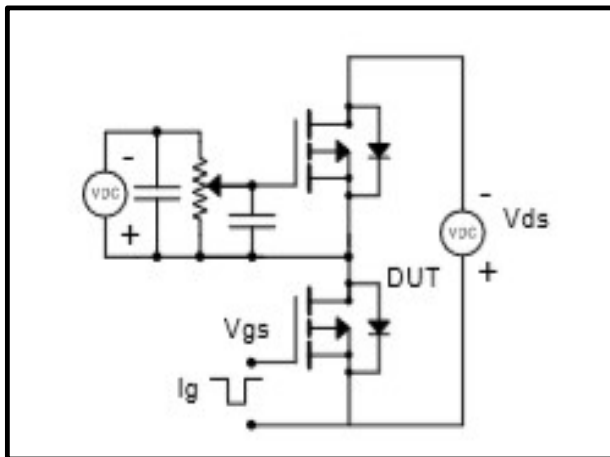


Fig.10 Gate Charge Waveform

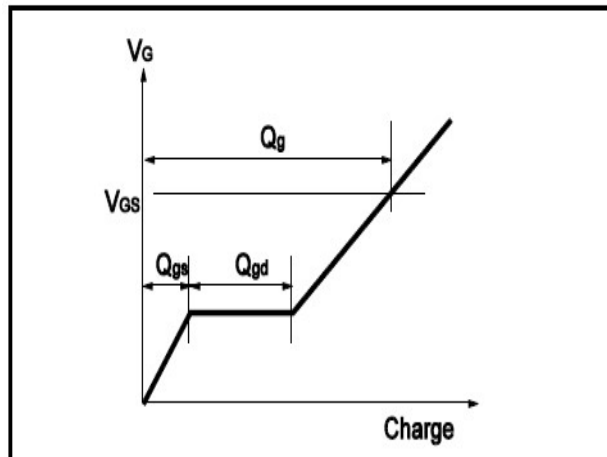


Fig.11 Switching Time Measurement Circuit

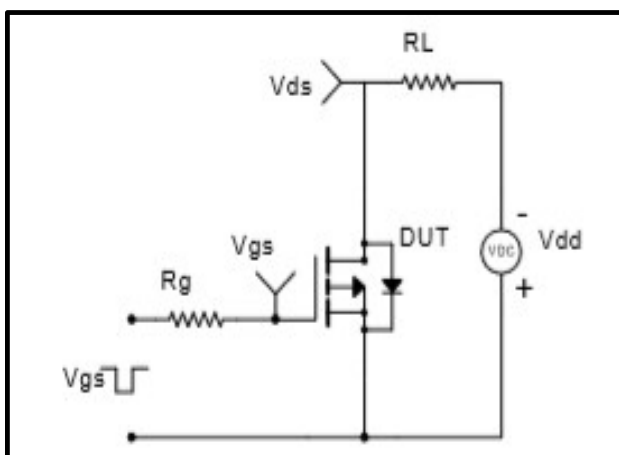
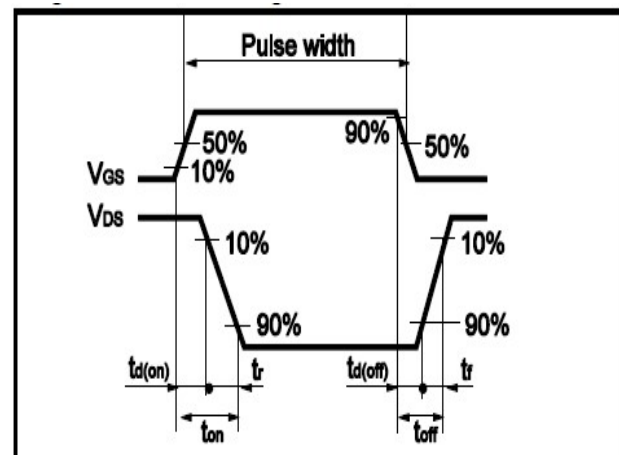


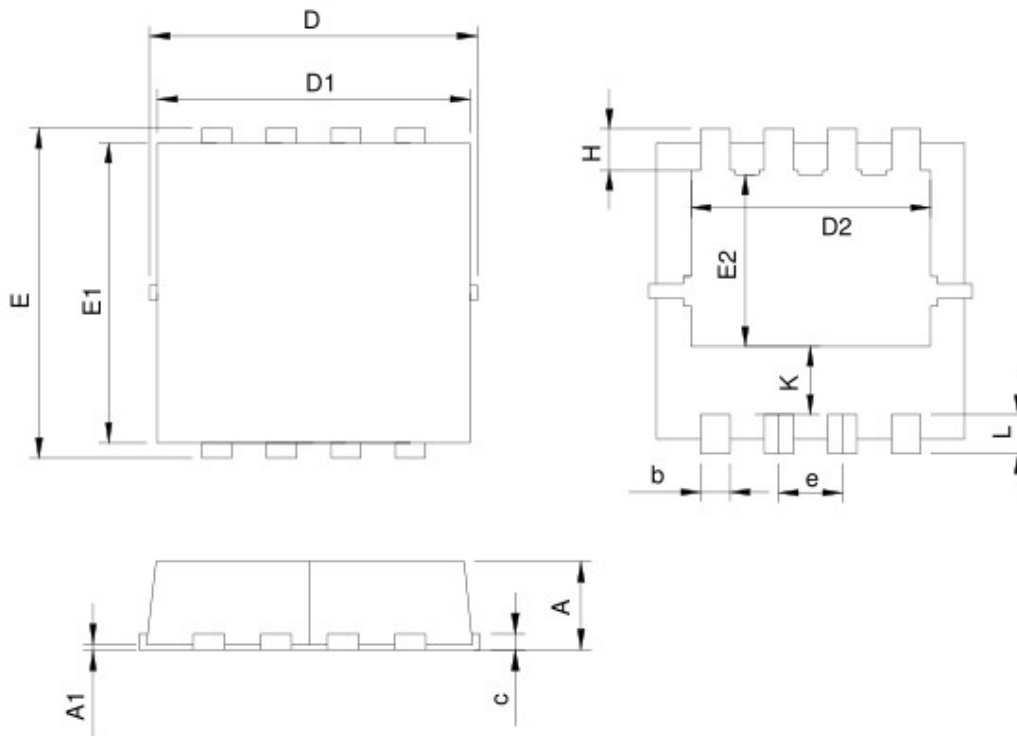
Fig.12 Switching Time Waveform





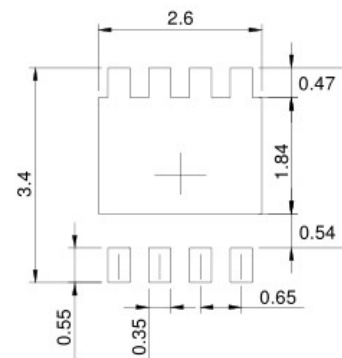
•Dimensions(DFN3×3)

Unit: mm



SYMBOL	DFN3.3x3.3-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
b	0.25	0.35	0.010	0.014
c	0.14	0.20	0.006	0.008
D	3.10	3.50	0.122	0.138
D1	3.05	3.25	0.120	0.128
D2	2.35	2.55	0.093	0.100
E	3.10	3.50	0.122	0.138
E1	2.90	3.10	0.114	0.122
E2	1.64	1.84	0.065	0.072
e	0.65 BSC		0.026 BSC	
H	0.32	0.52	0.013	0.020
K	0.59	0.79	0.023	0.031
L	0.25	0.55	0.010	0.022

RECOMMENDED LAND PATTERN



UNIT: mm